

AMENDMENTS TO THE SPECIFICATION

Page 6, first full paragraph at lines 6-21:

However, during the nitridation process, a portion of the top face of the semiconductor substrate 210 near the isolation trench 205 is also nitrided so that the nitrided oxide 214 is formed on the portion of the top face of the semiconductor substrate 210. As a result, the nitridation on the portion of the top face of the semiconductor substrate 210 prevents a gate oxide ~~215~~ 218 being grown up during a post process for forming the gate oxide 218. Accordingly, the gate oxide 218 above the portion of the top face of the semiconductor substrate 210 has relatively a thin thickness in comparison with the other portions of the gate oxide 218, which is called a gate oxide thinning phenomenon. This thin gate oxide 218 may increase the likelihood of dielectric breakdown, which can deteriorate the characteristic of the device formed in the active area. Furthermore, it is difficult to expect a reliable device in the long run.

Page 10, first full paragraph at lines 2-15:

Following the formation of the pad nitride 314 and the pad oxide 312, the photoresist masks are removed by using a typical removal method such as a photostrip process. Thereafter, the semiconductor substrate 310 is etched by using a dry etch

process employing the pad nitride 314 ~~316~~ as an etch mask so as to form an isolation trench 305 with a depth ranging from about 1,000 Å to about 2,500 Å. During the dry etch process, there may be lattice defects of silicon or damage on a surface of the isolation trench 305, which may incur a leakage current. In order to compensate the above damage, a wall oxide 316 is formed on a bottom and sidewalls of the isolation trench 305 with the thickness in the range of about 10 Å to about 135 Å, by thermally oxidizing the surface of the isolation trench 305.

Pages 15-16, the paragraph bridging the pages:

Following the formation of the pad nitride 414 and the pad oxide 412, the photoresist masks are removed by using a typical removal method such as a photostrip process. Thereafter, the semiconductor substrate 410 is etched by using a dry etch process employing the pad nitride 414 ~~416~~ as an etch mask so as to form an isolation trench 405 with a depth ranging from about 1,000 Å to about 2,500 Å. During the dry etch process, there may be lattice defects of silicon or damage on a surface of the isolation trench 405, which may incur a leakage current. In order to compensate the above damage, a wall oxide 416 is formed on a bottom and sidewalls of the isolation trench 405 with the thickness in the range of about 10 Å to about 135 Å, by thermally oxidizing the surface of the isolation trench 405.